

SEMITOP® 3

3-phase bridge rectifier + brake chopper

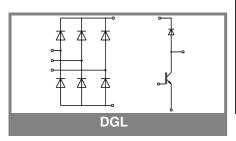
SK 95 DGL 126

Features

- · Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded alumium oxide ceramic (DCB)
- Trench IGBT technology
- CAL Technology FWD

Typical Applications*

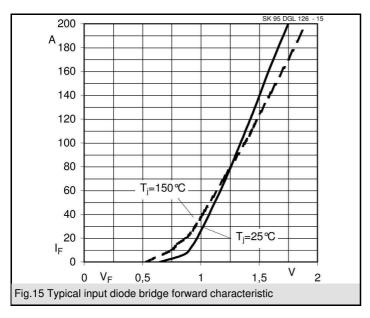
Rectifier

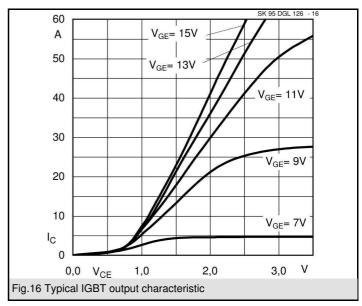


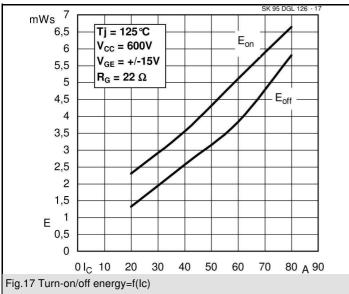
Absolute Maximum Ratings T _s = 25°C, unless otherwise specified							
Symbol	Conditions	Values	Units				
IGBT - Chopper							
V_{CES}		1200	V				
I _C	T _s = 25 (80) °C	40 (32)	Α				
I _{CRM}	$I_{CRM} = 2 \times I_{Cnom}, t_p = 1 \text{ ms}$	70	Α				
V_{GES}		±20	V				
T _j		-40 + 150	°C				
Diode - Chopper							
I _F	T _s = 25 (80) °C	45 (35)	Α				
I _{FRM}	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$	100	Α				
T _j		-40 + 150	°C				
Rectifier							
V_{RRM}		1600	V				
I _D	$T_s = 80 ^{\circ}C$	96	Α				
I _{FSM} / I _{TSM}	$t_p = 10 \text{ ms}$, sin 180 °, $T_i = 25 \text{ °C}$	700	Α				
I ² t	t _p = 10 ms , sin 180 ° ,T _i = 25 °C	2450	A²s				
T _j		-40 + 150	°C				
T _{sol}	Terminals, 10s	260	°C				
T _{stg}		-40 + 125	°C				
V _{isol}	AC, 1 min. / 1s	2500 / 3000	V				

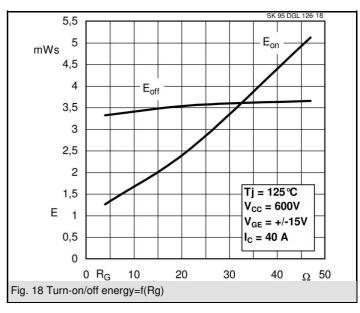
Characteristics		T _s = 25°C, unless otherwise specified						
Symbol	Conditions	min.	typ.	max.	Units			
IGBT - Chopper								
$\begin{array}{c} V_{CEsat} \\ V_{GE(th)} \\ V_{CE(TO)} \\ r_T \\ C_{ies} \\ C_{oes} \\ C_{res} \\ R_{th(j-s)} \\ \hline t_{d(on)} \\ t_r \\ t_{d(off)} \\ t_f \end{array}$	$\begin{split} &I_{C} = 35 \text{ A}, \ T_{j} = 25 \ (125) \ ^{\circ}\text{C} \\ &V_{GE} = V_{CE}, \ I_{C} = 1,5 \ \text{mA} \\ &T_{j} = 25 \ ^{\circ}\text{C} \ (125) \ ^{\circ}\text{C} \\ &T_{j} = 25 \ ^{\circ}\text{C} \ (125) \ ^{\circ}\text{C} \\ &V_{CE} = 25 \ V_{GE} = 0 \ \text{V}, \ f = 1 \ \text{MHz} \\ &V_{CE} = 25 \ V_{GE} = 0 \ \text{V}, \ f = 1 \ \text{MHz} \\ &V_{CE} = 25 \ V_{GE} = 0 \ \text{V}, \ f = 1 \ \text{MHz} \\ &V_{CE} = 25 \ V_{GE} = 0 \ \text{V}, \ f = 1 \ \text{MHz} \\ &V_{CE} = 26 \ V_{GE} = 0 \ \text{V}, \ f = 1 \ \text{MHz} \\ &V_{CE} = 25 \ V_{GE} = 0 \ \text{V}, \ f = 1 \ \text{MHz} \\ &V_{CE} = 25 \ V_{GE} = 0 \ \text{V}, \ f = 1 \ \text{MHz} \\ &V_{CE} = 30 \ \text{A}, \ T_{j} = 125 \ ^{\circ}\text{C} \\ &R_{Gon} = R_{Goff} = 22 \ \Omega \end{split}$	5	1,7 (2) 5,8 1 (0,9) 20 (31) 2,4 0,5 0,4 85 30 430 90	2,1 6,5 1,2 26	V V MΩ nF nF nF K/W ns ns ns			
E _{on}	inductive load		4,6		mJ			
E _{off}			4,3		mJ			
Diode - C V _F = V _{EC} V _(TO) r _T R _{th(j-s)} I _{RRM} Q _{rr} E _{rr}	$\begin{split} &I_F=45\text{ A, T}_j=25(150)\text{ °C}\\ &T_j=\text{°C }(125)\text{ °C}\\ &T_j=\text{°C }(125)\text{ °C}\\ &\text{per diode}\\ &\text{under following conditions}\\ &I_F=50\text{ A, V}_R=600\text{ V}\\ &V_{GE}=0\text{ V, T}_j=125\text{ °C}\\ &\text{di}_{F/dt}=500\text{ A/}\mu\text{s} \end{split}$		1,5 (1,5) (0,92) (13,4) 30 10	1,77 (1,77)	V V mΩ K/W A μC mJ			
Diode rectifier								
V _F V _(TO) r _T R _{th(j-s)}	$I_F = 35 \text{ A}, T_j = 25(125) ^{\circ}\text{C}$ $T_j = 150 ^{\circ}\text{C}$ $T_j = 150 ^{\circ}\text{C}$ per diode		-	1,2 0,8 11 1,2	V V mΩ K/W			
Temperatur sensor								
R _{ts}	%, T _r = () °C		()		Ω			
Mechanic w			30	2,5	g Nm			
M _s	Mounting torque			2,5	INIII			

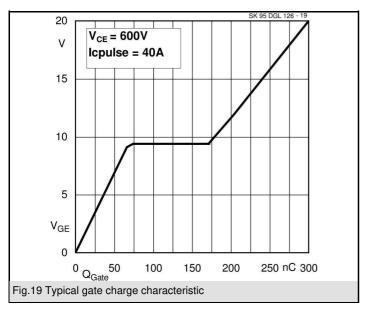
SK 95 DGL 126



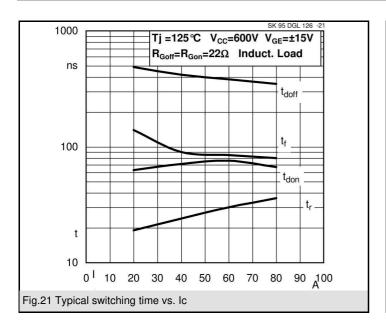


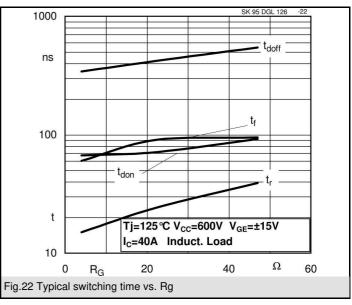




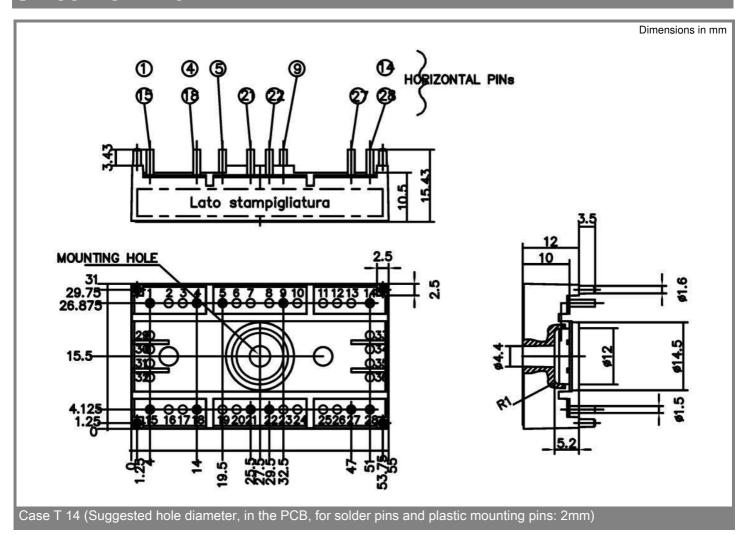


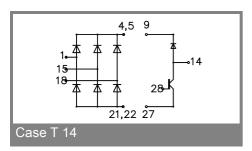
SK 95 DGL 126





3 19-09-2012 DIL © by SEMIKRON





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.